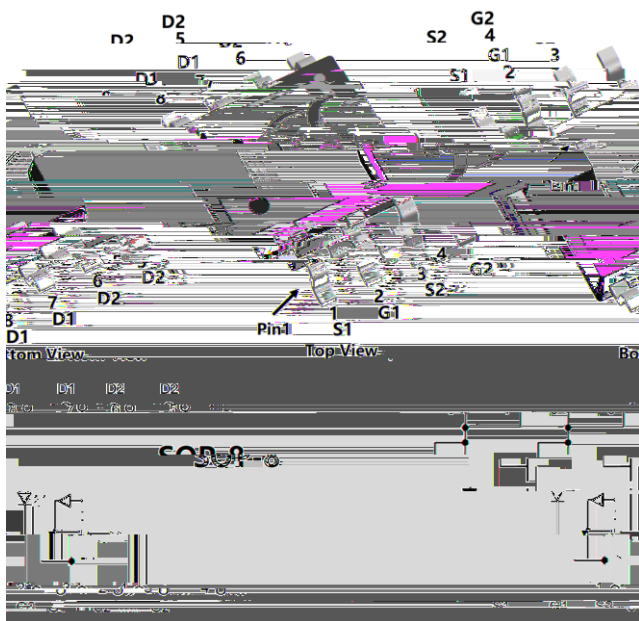




P-Channel and P-Channel Complementary



Product Summary

- V_{DS}
- I_D
- $R_{DS(ON)}$ (at $V_{GS}=-10V$)
- $R_{DS(ON)}$ (at $V_{GS}=-4.5V$)
- 100% EAS Tested

General Description

- Trench Power LV MOSFET
- High density cell design
- High Speed switching
- Moisture Sensitivity
- Epoxy Meets UL 94V-0
- Halogen Free

Applications

- Battery protection
- Load switch
- Power management

■ Absolute Maximum Ratings ($T_A=25^\circ C$ unless otherwise noted)

Parameter	Symbol			
Drain-source Voltage	V_{DS}			
Gate-source Voltage	V_{GS}	± 20	V	
Drain Current	I_D	-10	A	$T_A=25^\circ C$



YJS7328B

■ Electrical Characteristics ($T_J=25$ unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
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Static Parameter



Typical Electrical and Thermal Characteristics Diagrams

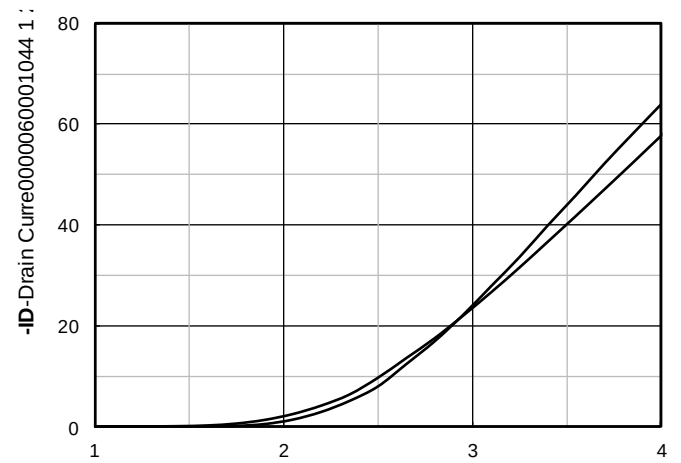
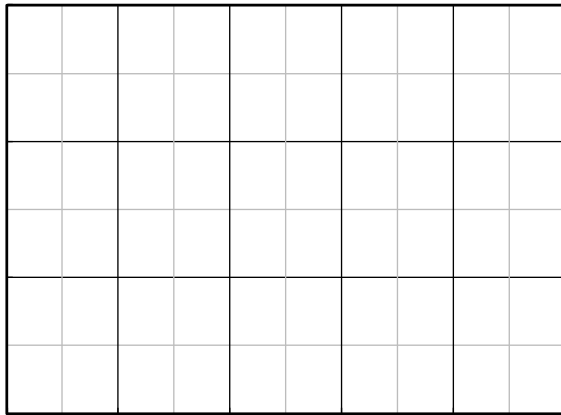


Figure 1. Output Characteristics

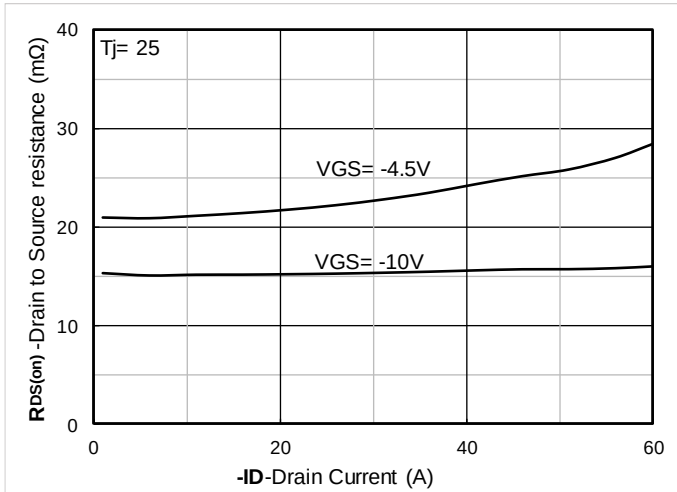


Figure 7. $R_{DS(on)}$ VS Drain Current

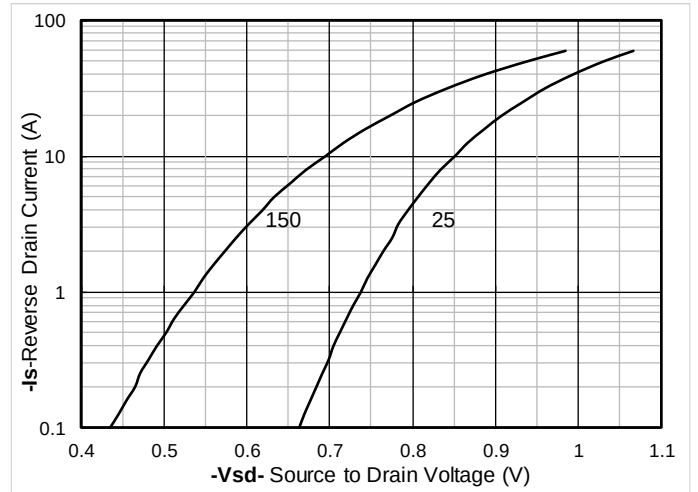


Figure 8. Forward characteristics of reverse diode

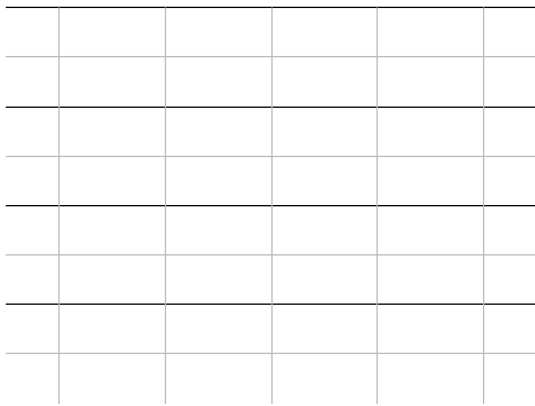


Figure 9. Normalized breakdown voltage

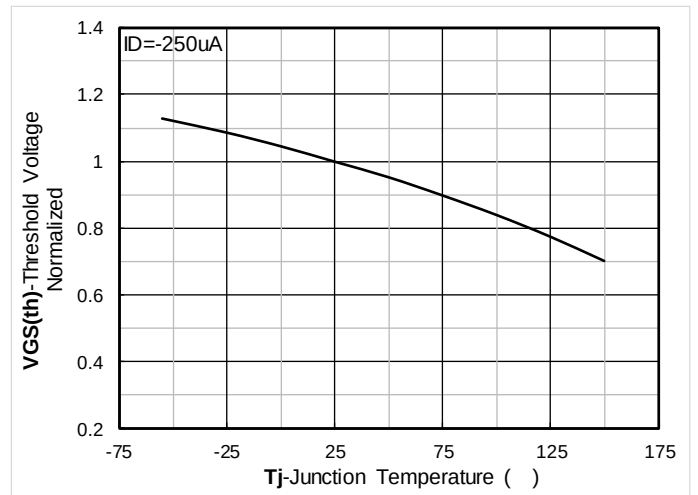
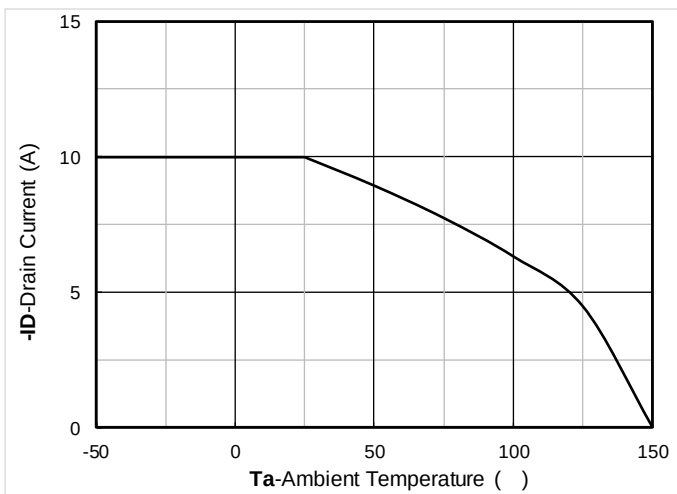
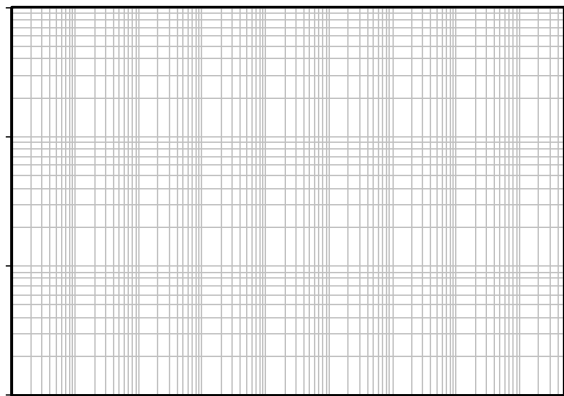


Figure 10. Normalized Threshold voltage







■ SOP-8 Package information

